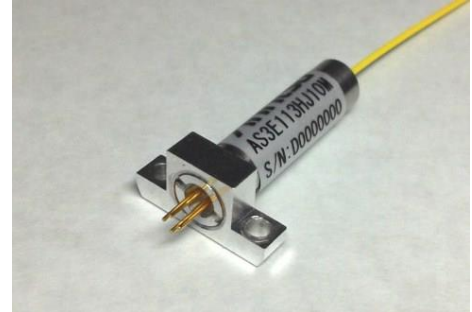


1.31μm SLD Module AS3E113HJ10M

AS3E113HJ10M is 1.3μm low power consumption SLD (Super-luminescent Diode) module developed as incoherent light sources for various optical measurements including Optical Coherence Tomography(OCT).

FEATURES

- Uncooled coaxial module.
- Optical output power (SMF) : 1mW
- Full Width at Half Maximum (FWHM): 53nm typ.

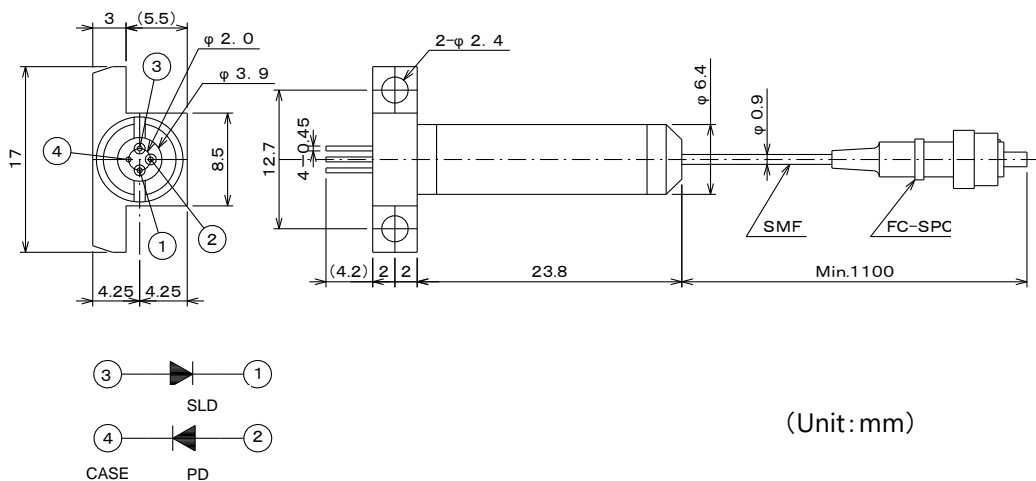


ABSOLUTE MAXIMUM RATINGS (T_{SOA}=25°C)

| Item | Symbol | Rating | Unit |
|----------------------------|------------------|------------|------|
| SLD Forward Current | I _F | 300 | mA |
| SLD Reverse Voltage | V _R | 2.0 | V |
| PD Reverse Voltage | V _{RD} | 15 | V |
| Operating Case Temperature | T _C | -5 to +75 | °C |
| Storage Temperature | T _{stg} | -40 to +85 | °C |

*Excess over the absolute maximum ratings may lead to damage.

DIMENSIONS



PIN CONFIGURATION

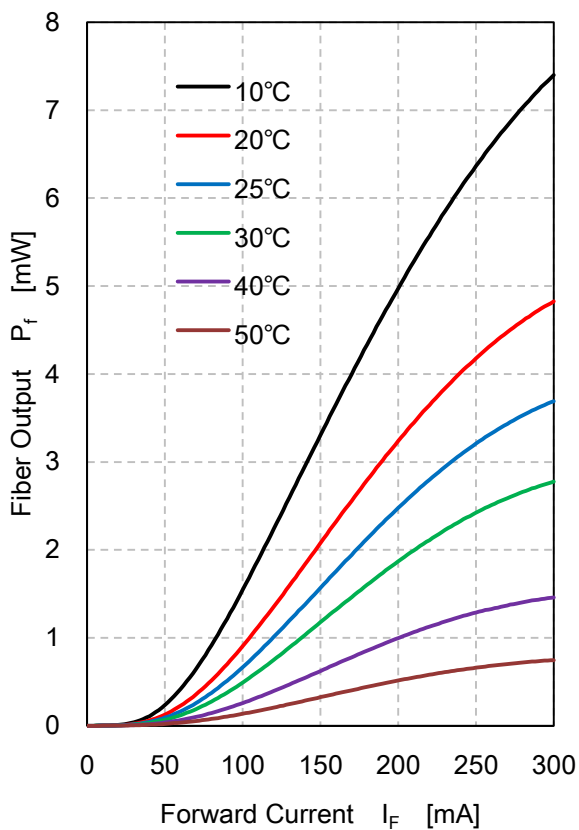
| No. | Functions |
|-----|-------------|
| 1 | SLD cathode |
| 2 | PD anode |
| 3 | SLD anode |
| 4 | PD cathode |

OPTICAL AND ELECTRICAL CHARACTERISTICS

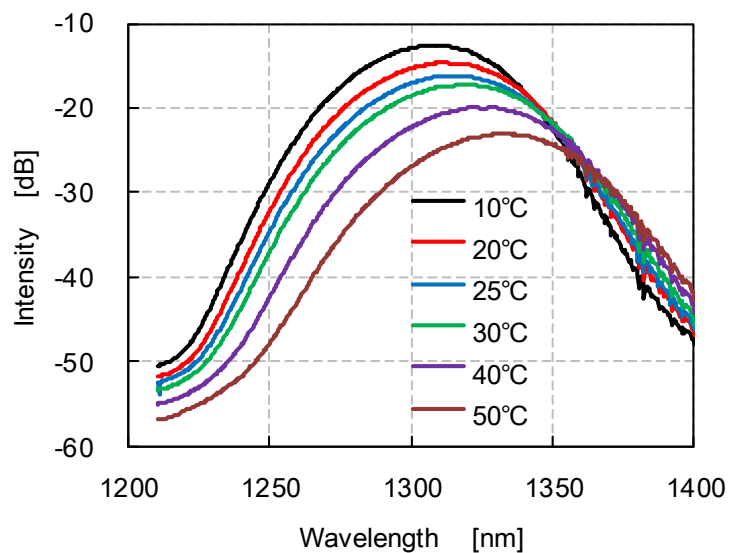
($T_{SLD}=25^{\circ}C$, $T_C=25^{\circ}C$)

| Item | Symbol | Test condition | Min. | Typ. | Max. | Unit |
|---------------------|-----------------|-------------------------------------|------|------|------|---------|
| Forward Voltage | V_F | $P_F=3mW$ | | | 2.0 | V |
| Forward Current | I_F | $P_F=3mW$ | | | 250 | mA |
| Center Wavelength | λ_C | $P_F=3mW$, -3dB | 1290 | 1310 | 1330 | nm |
| Spectral Half Width | $\Delta\lambda$ | $P_F=3mW$ | 50 | 53 | | nm |
| Spectral Ripple | M | $P_F=3mW$, res=0.1nm | | | 0.4 | dB |
| Monitor Current | I_m | $P_F=3mW$, $V_{RD}=5V$ | 500 | | 2500 | μA |
| PD Dark Current | I_d | $V_{RD}=5V$ | | | 0.1 | μA |
| Optical Isolation | R_o | $\lambda=1300nm$, $TC=25^{\circ}C$ | | 30 | | dB |

TYPICAL CHARACTERISTICS



Temperature characteristics of optical output



Temperature characteristics of spectrum



CAUTION : Handle the fiber of the enclosed device(s) with extreme care ; glass fiber is subject to breakage if mishandled and permanent damage to the device may result. Do not pull the device by the fiber or protective sleeve.
Do not coil the fiber into a loop of than 30 mm in radius.

| | |
|---|--|
| <p>SEMICONDUCTOR LASER</p> | |
| <p>AVOID EXPOSURE Invisible laser radiation is emitted from this aperture</p> | <p>INVISIBLE LASER RADIATION AVOID EYE OR SKIN EXPOSURE TO DIRECT OR SCATTERED RADIATION</p> <p>OUTPUT POWER 500mW WAVELENGTH 0.80 to 1.80 μm CLASS IIIb LASER PRODUCT</p> |
| <p>Caution - use of controls or adjustments or performance of procedures other than those specified herein may result in hazardous radiation exposure. This Product Complies with 21 CFR 1040.10 and 1040.11 Manufactured Anritsu Corp. 5-1-1 Onna, Atsugi-shi, Kanagawa, Japan</p> | |

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